## Brian M Bersch

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/8903914/publications.pdf

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		933264	1125617
13	906	10	13
papers	citations	h-index	g-index
13	13	13	1943
all docs	docs citations	times ranked	citing authors

#	Article	IF	CITATIONS
1	Tungsten Ditelluride: a layered semimetal. Scientific Reports, 2015, 5, 10013.	1.6	186
2	Realizing Large-Scale, Electronic-Grade Two-Dimensional Semiconductors. ACS Nano, 2018, 12, 965-975.	7.3	172
3	Tuning the Electronic and Photonic Properties of Monolayer MoS <sub>2</sub> via In Situ Rhenium Substitutional Doping. Advanced Functional Materials, 2018, 28, 1706950.	7.8	137
4	Atomically thin half-van der Waals metals enabled by confinement heteroepitaxy. Nature Materials, 2020, 19, 637-643.	13.3	114
5	Epitaxial graphene/silicon carbide intercalation: a minireview on graphene modulation and unique 2D materials. Nanoscale, 2019, 11, 15440-15447.	2.8	85
6	Considerations for Utilizing Sodium Chloride in Epitaxial Molybdenum Disulfide. ACS Applied Materials & Samp; Interfaces, 2018, 10, 40831-40837.	4.0	58
7	Impact of Postâ€Lithography Polymer Residue on the Electrical Characteristics of MoS <sub>2</sub> and WSe <sub>2</sub> Field Effect Transistors. Advanced Materials Interfaces, 2019, 6, 1801321.	1.9	56
8	Selective-area growth and controlled substrate coupling of transition metal dichalcogenides. 2D Materials, 2017, 4, 025083.	2.0	36
9	Deconvoluting the Photonic and Electronic Response of 2D Materials: The Case of MoS2. Scientific Reports, 2017, 7, 16938.	1.6	23
10	Unexpected Near-Infrared to Visible Nonlinear Optical Properties from 2-D Polar Metals. Nano Letters, 2020, 20, 8312-8318.	<b>4.</b> 5	22
11	Modification of the Electronic Transport in Atomically Thin WSe <sub>2</sub> by Oxidation. Advanced Materials Interfaces, 2020, 7, 2000422.	1.9	11
12	Scalable Characterization of 2D Gallium-Intercalated Epitaxial Graphene. ACS Applied Materials & Samp; Interfaces, 2021, 13, 55428-55439.	4.0	5
13	2D Materials: Tuning the Electronic and Photonic Properties of Monolayer MoS2 via In Situ Rhenium Substitutional Doping (Adv. Funct. Mater. 16/2018). Advanced Functional Materials, 2018, 28, 1870105.	7.8	1